

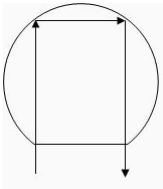
Part Number

Customer

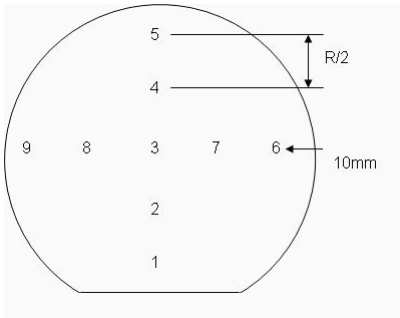
Category	Parameter	Specification	Measurement Method
OverallWafer	1.0	Silicon Supplier	Silicon Materials
	2.0	Diameter	150.00 +/- 0.50 mm
	3.0	Primary Flat Orientation	{110} +/- 0.5 degree
	4.0	Primary Flat Length	57.50 +/- 2.50 mm
	5.0	Secondary Flat Orientation	none
	6.0	Edge Rounding	Semi M1
	7.0	Overall Thickness	469.00 +/- 31.00 μ m
	8.0	Total Thickness Variation (TTV)	<5.00 μ m
	10.0	Bow	<50.00 μ m
	11.0	Warp	<50.00 μ m
	12.0	Edge Chips	0
	13.0	Edge Exclusion	5mm
	14.0	Handle Growth Method	CZ
HandleSilicon	15.0	Handle Orientation	{100} +/- 1 degree
	16.0	Handle Doping Type	ANY
	17.0	Handle Dopant	ANY
	18.0	Handle Resistivity	>1 Ohmcm
	19.0	Handle Thickness	450.00 +/- 30.00 μ m
	20.0	Backside Finish	lapped with oxide and scribe
	25.0	Oxide Type	10,000.00 +/- 1,000.00
BuriedOxide	32.0	Device Growth Method	CZ
	33.0	Device Orientation	{100} +/- 0.5 degree
	34.0	Device Doping Type	N
	35.0	Device Dopant	Phosphorous
	36.0	Device Resistivity	1 - 3 Ohmcm
	37.0	Nominal Thickness	18.00 +/- 0.75 μ m
	38.0	Distance to device silicon edge from wafer edge	<2mm
	39.0	Surface	roughness < 3A rms
	40.0	Voids	none inside 5mm edge exclusion
	41.0	Scratches	none
	42.0	Haze	none

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Category	Parameter	Specification	Measurement Method
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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information